

Vishay Siliconix

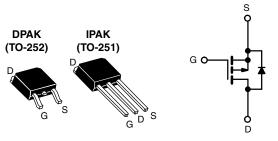
RoHS

COMPLIANT

HALOGEN

FREE

### Power MOSFET



P-Channel MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-60			
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = -10 V 0.28			
Q <sub>g</sub> (Max.) (nC)	19			
Q <sub>gs</sub> (nC)	5.4			
Q <sub>gd</sub> (nC)	11			
Configuration	Sin	gle		

#### **FEATURES**

- Dynamic dV/dt rating
- · Repetitive avalanche rated
- Surface-mount (IRFR9024, SiHFR9024)
- Straight lead (IRFU9024, SiHFU9024)
- · Available in tape and reel
- P-channel
- · Fast switching
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The DPAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU, SiHFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 W are possible in typical surface-mount applications.

ORDERING INFORMATION						
Package	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	DPAK (TO-252)	IPAK (TO-251)	
Lead (Pb)-free	SiHFR9024-GE3	SiHFR9024TR-GE3 a	SiHFR9024TRL-GE3 a	SiHFR9024TRR-GE3 a	SiHFU9024-GE3	
and halogen-free	IRFR9024PbF-BE3	IRFR9024TRPbF-BE3	IRFR9024TRLPbF-BE3		-	
Lead (Pb)-free	IRFR9024PbF	IRFR9024TRPbF a	IRFR9024TRLPbF a	=	IRFU9024PbF	

#### Note

a. See device orientation

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V <sub>DS</sub>	-60	V
Gate-source voltage			$V_{GS}$	± 20	7 v
Continuous drain surrent	V at 10 V	T <sub>C</sub> = 25 °C	,	-8.8	
Continuous drain current $V_{GS} \text{ at -10 V} \frac{T_C = 25 \text{ °C}}{T_C = 100 \text{ °C}}$			I <sub>D</sub>	-5.6	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	-35	1
Linear derating factor				0.33	W/°C
Linear derating factor (PCB mount) e				0.020	VV/ C
Single pulse avalanche energy b			E <sub>AS</sub>	300	mJ
Repetitive avalanche current a			I <sub>AR</sub>	-8.8	А
Repetitive avalanche energy <sup>a</sup>			E <sub>AR</sub>	5.0	mJ
Maximum power dissipation	T <sub>C</sub> =	25 °C	Б	42	W
Maximum power dissipation (PCB mount) e T <sub>A</sub> = 25 °C			P <sub>D</sub>	2.5	\ \v
Peak diode recovery dV/dt c			dV/dt	-4.5	V/ns
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) d	For	10 s	-	260	7

#### **Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b.  $V_{DD}=$  25 V, starting  $T_J=$  25 °C, L= 4.5 mH,  $R_g=$  25  $\Omega$ ,  $I_{AS}=$  8.8 A (see fig. 12) c.  $I_{SD}\leq$  11 A,  $dI/dt\leq$  140 A/ $\mu$ s,  $V_{DD}\leq$   $V_{DS}$ ,  $V_{DS}=$  150 °C
- 1.6 mm from case
- e. When mounted on 1" square PCB (FR-4 or G-10 material)

S21-0771-Rev. E, 19-Jul-2021 Document Number: 91278

# IRFR9024, IRFU9024, SiHFR9024, SiHFU9024

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THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	-	110	
Maximum junction-to-ambient (PCB mount) <sup>a</sup>	R <sub>thJA</sub>	-	-	50	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	-	3.0	

#### Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	- 60	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference	Reference to 25 °C, I <sub>D</sub> = 1 mA		- 0.063	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	- 2.0	-	- 4.0	V
Gate-source leakage	I <sub>GSS</sub>	,	V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zoro gata voltaga drain current	I	V <sub>DS</sub> =	- 60 V, V <sub>GS</sub> = 0 V	-	-	- 100	μA
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = -48 \text{ V}$	$V_{\rm S} = 0 \ V_{\rm N}  T_{\rm J} = 125 \ ^{\circ}{\rm C}$	-	-	- 500	μΑ
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 5.3 A <sup>b</sup>	=	-	0.28	Ω
Forward transconductance	9 <sub>fs</sub>	V <sub>DS</sub> =	- 25 V, I <sub>D</sub> = - 5.3 A	2.9	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>		$V_{GS} = 0 V$ ,	-	570	-	
Output capacitance	C <sub>oss</sub>		$V_{DS} = -25 V$ ,	-	360	-	рF
Reverse transfer capacitance	C <sub>rss</sub>	7	f = 1.0 MHz		65	-	
Total gate charge	Qg			-	-	19	
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V		=	-	5.4	nC
Gate-drain charge	Q <sub>gd</sub>			-	-	11	
Turn-on delay time	t <sub>d(on)</sub>			-	13	-	
Rise time	t <sub>r</sub>	$V_{DD}$ = - 30 V, $I_{D}$ = - 11 A, $R_{g}$ = 18 $\Omega$ , $R_{D}$ = 2.5 $\Omega$ , see fig. 10 <sup>b</sup>		-	68	-	
Turn-off delay time	t <sub>d(off)</sub>			-	15	-	ns
Fall time	t <sub>f</sub>		1		29	-	
Internal drain inductance	L <sub>D</sub>	Between 6 mm (0.25	') from	-	4.5	-	-11
Internal source inductance	L <sub>S</sub>	package and die cont	~\I — /	-	7.5	-	nH
Drain-Source Body Diode Characteristic	cs	•					
Continuous source-drain diode current	I <sub>S</sub>	MOSFET sym showing the		ı	-	- 8.8	A
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>	integral reverse p - n junction diode		-	-	- 35	
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C,	$I_S = -8.8 \text{ A}, V_{GS} = 0 \text{ V}^b$	-	-	- 6.3	V
Body diode reverse recovery time	t <sub>rr</sub>	T - 25 °C 1	11_AdI/dt100_A/::ch	-	100	200	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	1J = 25 C, IF	= - 11 A, dl/dt = 100 A/μs <sup>b</sup>	-	0.32	0.64	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic tu	rn-on time is negligible (turn	-on is dor	minated b	y L <sub>S</sub> and	L <sub>D</sub> )

#### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width  $\leq$  300  $\mu$ s; duty cycle  $\leq$  2 %

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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

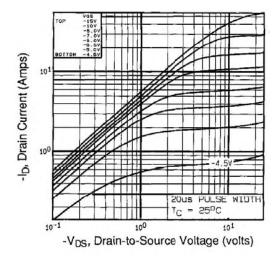


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

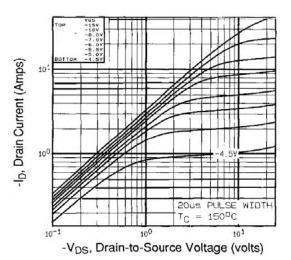


Fig. 2 -Typical Output Characteristics, T<sub>C</sub> = 150 °C

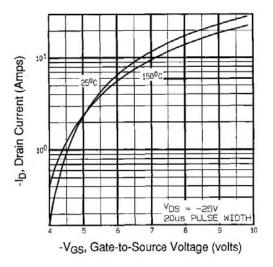


Fig. 3 - Typical Transfer Characteristics

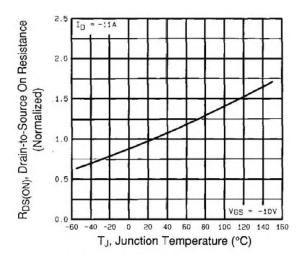


Fig. 4 - Normalized On-Resistance vs. Temperature

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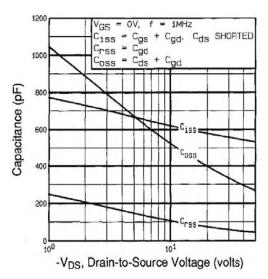


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

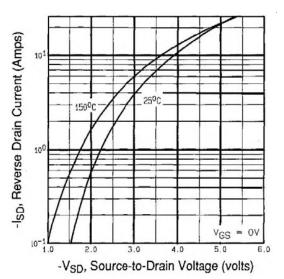


Fig. 7 - Typical Source-Drain Diode Forward Voltage

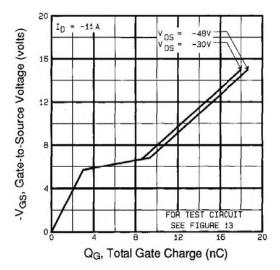


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

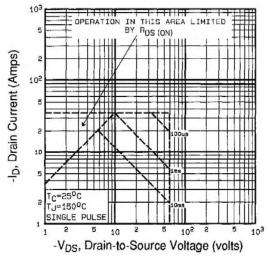


Fig. 8 - Maximum Safe Operating Area

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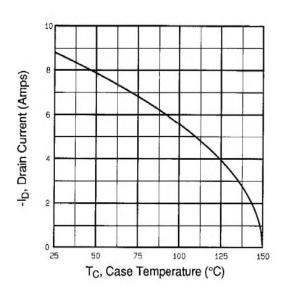


Fig. 9 - Maximum Drain Current vs. Case Temperature

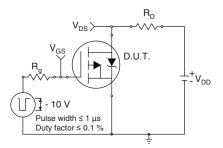


Fig. 10a - Switching Time Test Circuit

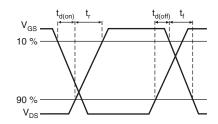


Fig. 10b - Switching Time Waveforms

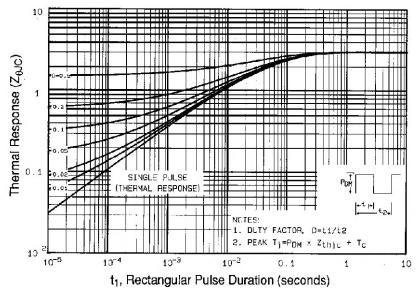


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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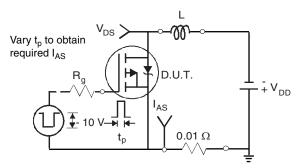


Fig. 12a - Unclamped Inductive Test Circuit

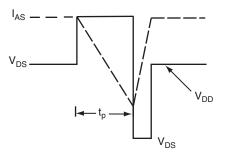


Fig. 12b - Unclamped Inductive Waveforms

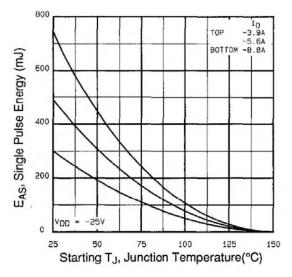


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

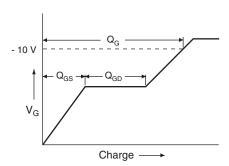


Fig. 13a - Basic Gate Charge Waveform

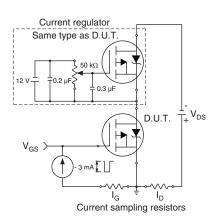
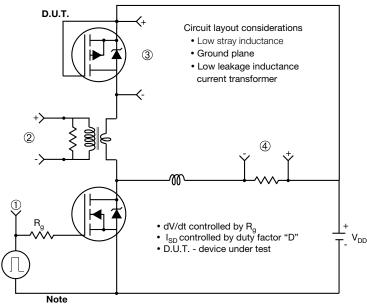


Fig. 13b - Gate Charge Test Circuit

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#### Peak Diode Recovery dV/dt Test Circuit



• Compliment N-Channel of D.U.T. for driver

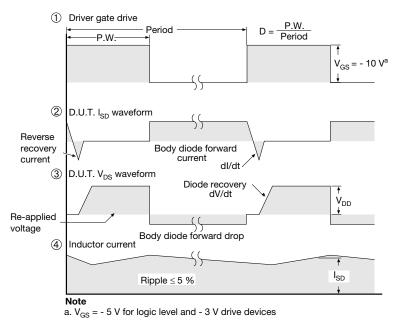


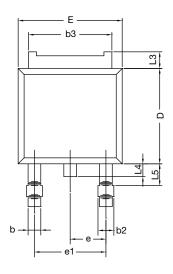
Fig. 14 - For P-Channel

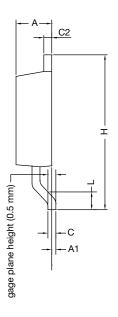
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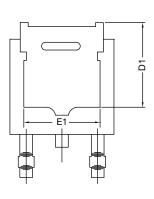


TO-252AA Case Outline

#### **VERSION 1: FACILITY CODE = Y**







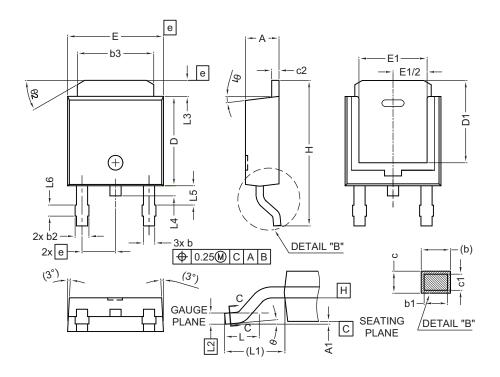
	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.38	
A1	-	0.127	
b	0.64	0.88	
b2	0.76	1.14	
b3	4.95	5.46	
С	0.46	0.61	
C2	0.46	0.89	
D	5.97	6.22	
D1	4.10	-	
E	6.35	6.73	
E1	4.32	-	
Н	9.40	10.41	
е	2.28	BSC	
e1	4.56	BSC	
L	1.40	1.78	
L3	0.89	1.27	
L4	- 1.02		
L5	1.01	1.52	

#### Note

• Dimension L3 is for reference only



#### **VERSION 2: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	2.18	2.39	
A1	-	0.13	
b	0.65	0.89	
b1	0.64	0.79	
b2	0.76	1.13	
b3	4.95	5.46	
С	0.46	0.61	
c1	0.41	0.56	
c2	0.46	0.60	
D	5.97	6.22	
D1	5.21	=	
E	6.35	6.73	
E1	4.32 -		
е	2.29 BSC		
Н	9.94	10.34	

	MILLIMETERS		
DIM.	MIN.	MAX.	
L	1.50	1.78	
L1	2.74	ł ref.	
L2	0.51	BSC	
L3	0.89	1.27	
L4	-	1.02	
L5	1.14	1.49	
L6	0.65	0.85	
θ	0°	10°	
θ1	0°	15°	
θ2	25°	35°	

#### Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

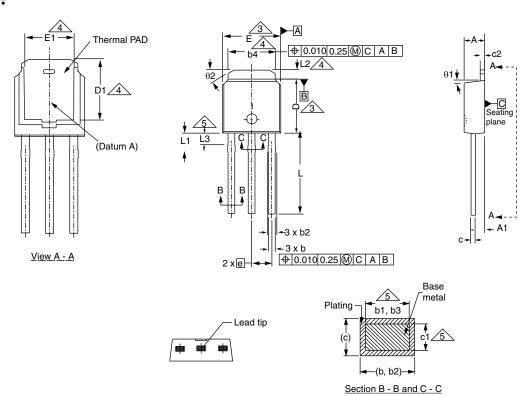
ECN: E19-0649-Rev. Q, 16-Dec-2019

DWG: 5347

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# **Case Outline for TO-251AA (High Voltage)**

#### **OPTION 1:**



	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
Α	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
Е	6.35	6.73	0.250	0.265
E1	4.32	=	0.170	=
е	2.29	2.29 BSC		BSC
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
θ1	0'	15'	0'	15'
θ2	25'	35'	25'	35'
	•		•	

ECN: E21-0682-Rev. C, 27-Dec-2021

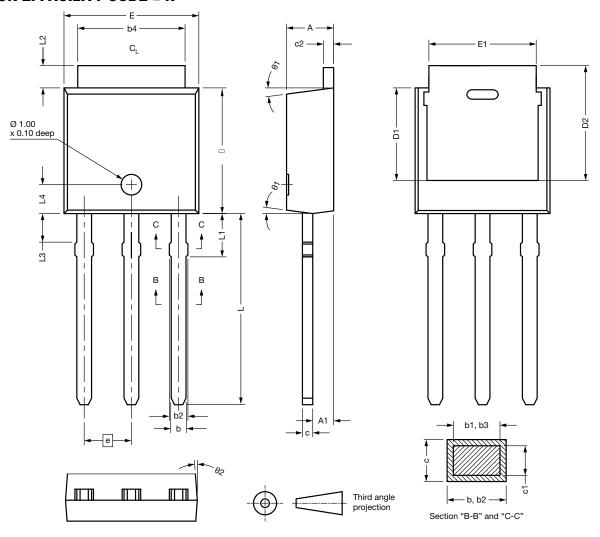
DWG: 5968

#### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension are shown in inches and millimeters
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Thermal pad contour optional with dimensions b4, L2, E1 and D1
- Lead dimension uncontrolled in L3
- Dimension b1, b3 and c1 apply to base metal only
- Outline conforms to JEDEC® outline TO-251AA



#### **OPTION 2: FACILITY CODE = N**



DIM.	MIN.	NOM.	MAX.
Α	2.180	2.285	2.390
A1	0.890	1.015	1.140
b	0.640	0.765	0.890
b1	0.640	0.715	0.790
b2	0.760	0.950	1.140
b3	0.760	0.900	1.040
b4	4.950	5.205	5.460
С	0.460	1	0.610
c1	0.410	-	0.560
c2	0.460	-	0.610
D	5.970	6.095	6.220
D1	4.300	- 1	ı

DIM.	MIN.	NOM.	MAX.
D2	5.380	-	-
E	6.350	6.540	6.730
E1	4.32	-	-
е	2.29	BSC	
L	8.890	9.270	9.650
L1	1.910	2.100	2.290
L2	0.890	1.080	1.270
L3	1.140	1.330	1.520
L4	1.300	1.400	1.500
θ1	0°	7.5°	15°
θ2	4°	-	-

ECN: E21-0682-Rev. C, 27-Dec-2021

DWG: 5968

#### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- All dimension are in millimeters, angles are in degrees
- Heat sink side flash is max. 0.8 mm



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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